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Single Quantum Dot Rectifying Diode With Tunable Threshold Voltage

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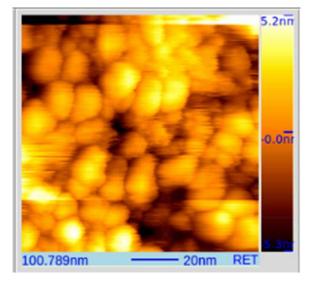


Figure S1. STM microgram for ZnO surface with a device structure ITO/ZnO

QD/ITO interface

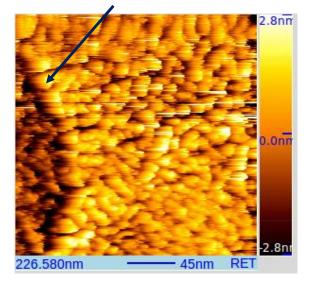


Figure S2. STM microgram for CdS (2% Co doped) surface with a device structure ITO/CdS.

Height difference in the interface indicates the monolayer formation on the substrate.

^{a.} Address here.

^{b.} Address here.

^{c.} Address here.

⁺ Footnotes relating to the title and/or authors should appear here.

Electronic Supplementary Information (ESI) available: [details of any supplementary information available should be included here]. See DOI: 10.1039/x0xx00000x

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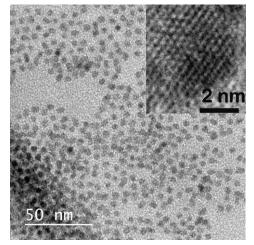


Figure S3. TEM picture of 4% doped CdS QDs . Inset shows the high resolution images of QD which clearly indicate the crystalline nature of QDs

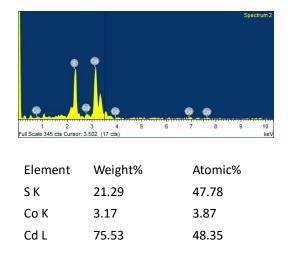


Figure S4. The energy dispersive X-ray analysis (EDXA) of this 4% doped QDs This data indicates the existence of Co around 3.87% in molar ratio

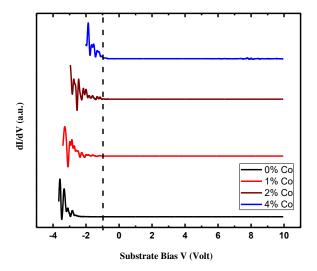


Figure S5. dl/dV Vs V plot for various Co doped CdS QDs with a device structure ITO/ZnO/CdS. Dotted line at V=-1V guided the variation of turn on conduction for different doped QD device.